

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A method of introducing impurity; wherein, in the course of introducing a material to a solid substance which has an oxidized film or other film sticking on the surface,

the oxidized film and other film are first removed as the surface treatment to the solid substance with ~~at least one means selected from among the group consisting of a means for irradiating the surface of solid substance with plasma, a means for irradiating the surface of solid substance with gas and~~ a means for dipping the surface of the solid substance in a reductive liquid, and then

a certain desired particle is attached or introduced.

2-3. Canceled

4. (Currently Amended) The method of introducing impurity recited in claim 1, wherein

the reductive liquid is at least one liquid ~~item~~ selected from ~~among~~ the group consisting of hydrogen fluoride, sodium hydroxide, aqueous ammonia, sulfinic acid, and adipic acid di-2-ethylhexyl ester, etc.

5. (Currently Amended) The method of introducing impurity recited in claim 1, wherein

the means for dipping the surface of solid substance in a reductive liquid rubs the surface of the solid substance mechanically when the solid substance ~~it~~ is dipped in the reductive liquid.

6. (Original) The method of introducing impurity recited in claim 1, wherein

the certain desired particle is attached or introduced by bringing a gas containing the certain desired particle to make contact to the surface of solid substance which surface has been made to be free of the oxidized film and other film, thereby the particle is attached or introduced to the surface, or the vicinity, of solid substance.

7. (Currently Amended) The method of introducing impurity recited in claim 1, wherein

the certain desired particle is attached or introduced by irradiating the surface of the solid substance, which surface has been made to be free of the oxidized film and other film, with an electromagnetic wave whose energy matches ~~is matching~~ the energy that is binding the hydrogen or hydroxyl radical sticking on the surface with the atom of the solid substance, thereby converting the binding into a non-coupled state, separating the sticking hydrogen or hydroxyl radical, and exposing the atom constituting the solid substance to the surface; and then introducing the certain desired particle for making contact so that the particle is attached or introduced to the surface, or the vicinity, of the solid substance.

8. (Currently Amended) The method of introducing impurity recited in claim 7, wherein

the energy of the irradiating electromagnetic wave is greater ~~stronger~~ than 318 kJ/mol, ~~not stronger and less~~ than 666 kJ/mol.

9. (Currently Amended) The method of introducing impurity recited in claim 8, wherein

the energy of the irradiating electromagnetic wave is ~~corresponds to~~ 425 kJ/mol or higher.

10. (Currently Amended) The method of introducing impurity recited in claim 1, wherein

the attaching or introducing of ~~a~~ the certain desired particle is conducted in an environment in which the temperature of the solid substance is lower than 600°C.

11. (Currently Amended) A method of introducing impurity; wherein, in the course

of introducing a material in the phase of ion, plasma, or gas, ~~etc.~~ to a solid substance which has an oxidized film or other film sticking to the surface,

the oxidized film and other film are first removed as the surface treatment to solid substance with ~~at least one means selected from among the group consisting of a means for irradiating the surface of solid substance with plasma, a means for irradiating the surface of solid substance with gas and a means for dipping the surface of solid substance in a reductive liquid, and then~~

a certain desired particle is attached or introduced.

12. (Original) The method of introducing impurity recited in claim 1, wherein

the certain desired particle is attached or introduced while it is in either one of the states among plasma, gas and ultra low-energy ion.

13. (Original) The method of introducing impurity recited in claim 1, wherein

at least one facility selected from among each of the following respective categories is used; at least one apparatus selected from among the group consisting of an apparatus for irradiating the surface of solid substance with plasma, an apparatus for irradiating the surface of solid substance with gas and an apparatus for dipping the surface of solid substance in a reductive liquid; an apparatus for bringing a gas containing a certain desired particle to the surface of solid substance; and an annealing apparatus for diffusing the certain desired particle attached or introduced therein.

14. (Original) The method of introducing impurity recited in claim 13, wherein

the apparatus for dipping the surface of solid substance in a reductive liquid is provided with a mechanism for rubbing the surface of solid substance mechanically.

15. Canceled

16. (Original) The method of introducing impurity recited in claim 13, wherein

at least two items selected from among the following categories are used in a combination mode or as an integration; at least one apparatus selected from among the

group consisting of an apparatus for irradiating the surface of solid substance with plasma, an apparatus for irradiating the surface of solid substance with gas and an apparatus for dipping the surface of solid substance in a reductive liquid; an apparatus for bringing a gas containing a certain desired particle to make contact with the surface of solid substance; and an annealing apparatus for diffusing the certain desired particle attached or introduced therein.

17. (Currently Amended) An active component device and a passive component device manufactured in accordance with a method of introducing impurity; wherein, in the course of introducing a material to a solid substance which has an oxidized film or other film sticking on the surface,

the oxidized film and other film are first removed as the surface treatment to the solid substance with ~~at least one means selected from among the group consisting of a means for irradiating the surface of solid substance with plasma, a means for irradiating the surface of solid substance with gas and a means for dipping the surface of solid substance in a reductive liquid,~~ and then

a certain desired particle is attached or introduced.

18.-33. Canceled

34. (Currently Amended) An impurity-containing component device manufactured through a procedure; wherein, in the course of introducing a material to a solid substance which has an oxidized film or other film sticking on the surface,

the oxidized film and other film are first removed as the surface treatment to the solid substance with ~~at least one means selected from among the group consisting of a means for irradiating the surface of solid substance with plasma, a means for irradiating the surface of solid substance with gas and a means for dipping the surface of solid substance in a reductive liquid,~~ and then

a certain desired particle is attached or introduced.

35. (Original) The impurity-containing component device recited in claim 34, wherein

the plasma is that of a rare argon gas, or a system containing hydrogen.

36. (Original) The impurity-containing component device recited in claim 34, wherein

the gas is that of a system containing hydrogen.

37. (Currently Amended) The impurity-containing component device recited in claim 34, wherein

the reductive liquid is at least one liquid ~~item~~ selected from ~~among~~ the group consisting of hydrogen fluoride, sodium hydroxide, aqueous ammonia, sulfinic acid, and adipic acid di-2-ethylhexyl ester, ~~etc.~~

38. (Currently Amended) The impurity-containing component device recited in claim 34, wherein

the means for dipping the surface of solid substance in a reductive liquid rubs the surface of the solid substance mechanically when the solid substance ~~it~~ is dipped in the reductive liquid.

39. (Currently Amended) The impurity-containing component device recited in claim 34, wherein

the method of attaching or introducing ~~a~~ the certain desired particle is bringing a gas containing a certain desired particle to make contact to the surface of solid substance, which surface has been made to be free of the oxidized film and other film, thereby attaching or introducing the particle to the surface, or the vicinity, of the solid substance.

40. (Currently Amended) The impurity-containing component device recited in claim 34, wherein

the method of attaching or introducing ~~a~~ the certain desired particle is irradiating the surface of solid substance, which surface has been made to be free of the oxidized film and other film, with an electromagnetic wave whose energy matches ~~is matching~~ the energy that is binding the hydrogen or hydroxyl radical sticking on the surface with the atom of solid

substance, thereby converting the binding into a non-coupled state, separating the sticking hydrogen or hydroxyl radical, and exposing the atom constituting solid substance to the surface; and then introducing the certain desired particle for making contact so that the particle is attached or introduced to the surface, or the vicinity, of the solid substance.

41. (Currently Amended) The impurity-containing component device recited in claim 40, wherein

the energy of the irradiating electromagnetic wave is greater~~stronger~~ than 318 kJ/mol, ~~not stronger and less~~ than 666 kJ/mol.

42. (Currently Amended) The impurity-containing component device recited in claim 41, wherein

the energy of the irradiating electromagnetic wave ~~is corresponds to~~ 425 kJ/mol or higher.

43. (Currently Amended) The impurity-containing component device recited in claim 34, wherein

the attaching or introducing of ~~a~~ the certain desired particle is conducted in an environment in which the temperature of solid substance is lower than 600°C.

44. (Currently Amended) An impurity-containing component device manufactured through a procedure; wherein, in the course of introducing a material in the phase of ion, plasma, or gas, ~~etc.~~ to a solid substance which has an oxidized film or other film sticking to the surface,

the oxidized film and other film are first removed as the surface treatment to the solid substance with ~~at least one means selected from among the group consisting of a means for irradiating the surface of solid substance with plasma, a means for irradiating the surface of solid substance with gas and~~ a means for dipping the surface of solid substance in a reductive liquid, and then

a certain desired particle is attached or introduced.

45. (Currently Amended) The impurity-containing component device recited in claim 40, wherein

the a-certain desired particle is attached or introduced while it is in either one of the states among plasma, gas and ultra low-energy ion.

46. (Original) The impurity-containing component device recited in claim 40 manufactured on an apparatus, which apparatus including at least one facility selected from among each of the following respective categories; at least one apparatus selected from among the group consisting of an apparatus for irradiating the surface of solid substance with plasma, an apparatus for irradiating the surface of solid substance with gas and an apparatus for dipping the surface of solid substance in a reductive liquid; an apparatus for bringing a gas containing a certain desired particle to the surface of solid substance; and an annealing apparatus for diffusing the certain desired particle attached or introduced therein.

47. (Original) The impurity-containing component device recited in claim 46, wherein

the apparatus for dipping the surface of solid substance in a reductive liquid is provided with a mechanism for rubbing the surface of solid substance mechanically.

48. (Currently Amended) The impurity-containing component device recited in claim 46, wherein

the apparatus for bringing a gas containing a certain desired particle to the surface of the solid substance is provided with a mechanism for irradiating with an electromagnetic wave whose energy matches ~~is matching~~ the energy that is binding the hydrogen or hydroxyl radical sticking on the surface of the solid substance, which surface has been made to be free of the oxidized film and other film, with the atom the of solid substance.

49. (Currently Amended) The impurity-containing component device recited in claim 46 manufactured on an apparatus, which apparatus including at least two items selected from the following categories in a combination mode or as an integration; at least one apparatus selected from among the group consisting of an apparatus for irradiating the surface of solid substance with plasma, an apparatus for irradiating the surface of solid

substance with gas and an apparatus for dipping the surface of solid substance in a reductive liquid; an apparatus for bringing a gas containing a certain desired particle to make contact with the surface of solid substance; and an annealing apparatus for diffusing the certain desired particle attached or introduced therein.

50. (Currently Amended) An active component device and a passive component device manufactured in accordance with a method of introducing impurity; wherein, in the course of introducing a material in the phase of ion, plasma, or gas, ~~etc.~~ to a solid substance which has an oxidized film or other film sticking to the surface,

the oxidized film and other film are first removed as the surface treatment to the solid substance with ~~at least one means selected from among the group consisting of a means for irradiating the surface of solid substance with plasma, a means for irradiating the surface of solid substance with gas and~~ a means for dipping the surface of solid substance in a reductive liquid, and then

a certain desired particle is attached or introduced.